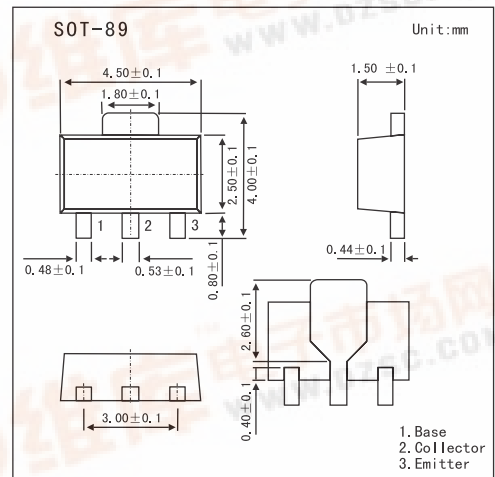


SMD Type Transistors

PNP Silicon Power Switching Transistor
FCX790A

■ Features

- 2W power dissipation.
- 6A peak pulse current.
- Excellent HFE characteristics.
- Low saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EB0}	-5	V
Continuous collector current	I _{CM}	-6	A
Peak pulse current	I _c	-2	A
Power dissipation	P _{tot}	1	W
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

FCX790A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A$	-50			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	$I_C = -10mA$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A$	-5			V
Collector-base cut-off current	I_{CBO}	$V_{CB} = -10V$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4V$			0.1	μA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = -0.5A, I_B = -5mA$ $I_C = -1A, I_B = -10mA$ $I_C = -2A, I_B = -50mA$			-250 -350 -450	mV
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = -1A, I_B = -10mA$			-0.9	V
Base-emitter ON voltage *	$V_{BE(on)}$	$I_C = -1A, V_{CE} = -2V$		-0.8		V
Static Forward Current Transfer Ratio *	h_{FE}	$I_C = -10mA, V_{CE} = -2V$ $I_C = -500mA, V_{CE} = -2V$ $I_C = -1A, V_{CE} = -2V$ $I_C = -2A, V_{CE} = -2V$	300 250 200 150	800		
Transitional frequency	f_T	$I_C = -50mA, V_{CE} = -5V, f = 50MHz$	100			MHz
Input capacitance	C_{ibo}	$V_{EB} = 0.5V, f = 1MHz$		225		pF
Output capacitance	C_{obo}	$V_{CB} = -10V, f = 1MHz$		24		pF
Turn-on time	$t_{(on)}$	$I_C = -500mA, V_{CC} = -10V$		35		ns
Turn-off time	$t_{(off)}$	$I_{B1} = I_{B2} = -50mA$		600		ns

* Pulse test: $t_p = 300\mu s$; $d \leq 0.02$.

■ Marking

Marking	790
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